

# NPN SILICON DARLINGTONS POWER TRANSISTORS

They are silicon epitaxial base transistors mounted in TO-3PN. They are designed for audio output stages and general amplifier and switching applications. complementary is BDV64-A- B-C Compliance to RoHS.

### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Ratings		Value	Unit	
		BDV65	60		
V <sub>CEO</sub>	Callantan Fraittan Valtana	BDV65A	80	V	
	Collector-Emitter Voltage	BDV65B	100	V	
		BDV65C	120		
		BDV65	60		
V	Collector Pose Voltage	BDV65A	80	V	
V <sub>CBO</sub>	Collector-Base Voltage	BDV65B	100	V	
		BDV65C	120		
	Emitter-Base Voltage	BDV65	5.0	V	
\ <u>\</u>		BDV65A			
V <sub>EBO</sub>		BDV65B			
		BDV65C			
	Collector Current	BDV65	12	А	
		BDV65A			
Ic		BDV65B			
		BDV65C			
Ісм	Collector Peak Current	BDV65	15		
		BDV65A			
		BDV65B	15		
		BDV65C			
I <sub>B</sub>	Dana Current	BDV65			
		BDV65A	0.5	^	
	Base Current	BDV65B	0.5	А	
		BDV65C			



### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Ratings			Value	Unit
	Power Dissipation	T <sub>mb</sub> = 25° C	BDV65	125	Watts
			BDV65A		
			BDV65B		
PT			BDV65C		
		T <sub>mb</sub> = 25° C	BDV65	3.5	
			BDV65A		
			BDV65B		
			BDV65C		
TJ	Junction Temperature		BDV65	150	•C
			BDV65A		
			BDV65B		
			BDV65C		
Ts	Storage Temperature		BDV65	65 to +150	
			BDV65A		
			BDV65B		
		BDV65C			

#### **THERMAL CHARACTERISTICS**

Symbol	Ratings		Value	Unit
	Thermal Resistance, Junction to Case  BDV65  BDV65A  BDV65B  BDV65C	BDV65	1	°C/W
R <sub>thj-c</sub>		BDV65A		
		BDV65B		
		BDV65C		
R <sub>thj-a</sub>	Thermal Resistance, Junction to Ambient	BDV65	35.7	
		BDV65A		
		BDV65B		
	BDV65C			



### **ELECTRICAL CHARACTERISTICS**

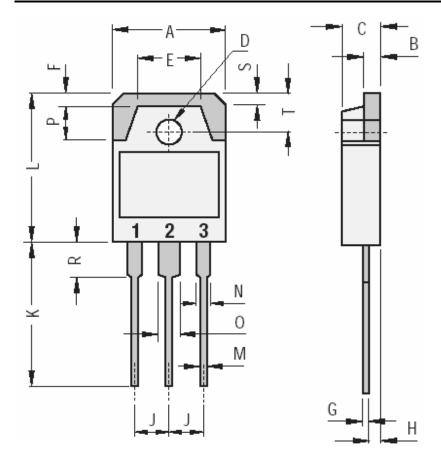
TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)		Min	Тур	Mx	Unit	
	Collector Cutoff Current	V <sub>CE</sub> = 30 V, I <sub>B</sub> = 0		BDV65		-	2	mA
I <sub>CEO</sub>		V <sub>CE</sub> = 40 V, I <sub>B</sub> = 0		BDV65A				
		V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0		BDV65B	<b>-</b>			
		$V_{CE} = 60 \text{ V}, I_{B} = 0$		BDV65C				
		VCE- 00 V, IB- 0		BDV65				
	Emitter Cutoff Current			BDV65A			_	
I <sub>EBO</sub>		$V_{BE}=5 V, I_{C}=0$		BDV65B	-	-	5	mA
				BDV65C				
			V <sub>CB</sub> = 60 V	BDV65			0.4	- mA
		I <sub>E</sub> = 0 T <sub>j</sub> =25°C	V <sub>CB</sub> = 80 V	BDV65A		-		
	Collector Cutoff Current		V <sub>CB</sub> = 100 V	BDV65B	-			
Ісво			V <sub>CB</sub> = 120 V	BDV65C				
		I <sub>E</sub> = 0 T <sub>i</sub> =150°C	V <sub>CB</sub> = 30 V	BDV65		-	2	
			V <sub>CB</sub> = 40 V	BDV65A				
			V <sub>CB</sub> = 50 V	BDV65B	- -			
		,	V <sub>CB</sub> = 60 V	BDV65C				
V <sub>CEO</sub>	Collector-Emitter Breakdown Voltage (*)	I <sub>C</sub> = 30 mA, I <sub>B</sub> = 0		BDV65	60	-	-	V
				BDV65A	80	-		
				BDV65B	100	-	-	
				BDV65C	120	-	-	
h <sub>FE</sub>	DC Current Gain (*)	V <sub>CE</sub> = 4 V, I <sub>C</sub> = 5 A B		BDV65	_	-	-	-
				BDV65A	1000			
				BDV65B	_ 1000			
				BDV65C				
V <sub>CE(SAT)</sub>	Collector-Emitter saturation Voltage (*)	I <sub>C</sub> = 5 A, I <sub>B</sub> = 20 mA		BDV65	- - -	-	2	V
				BDV65A				
				BDV65B				
	Base-Emitter Voltage(*)	V <sub>CE</sub> = 4 V, I <sub>C</sub> = 5 A		BDV65C		-	2,5	V
				BDV65 BDV65A	-			
$V_{BE}$				BDV65A	<b>⊣</b> -			
	Voltage( )			BDV65C				

<sup>(\*)</sup> Pulse Width  $\approx 300~\mu s,$  Duty Cycle  $\angle$  1.5 %



### **MECHANICAL DATA CASE TO3PN Non Isolated Plastic Package**



DIMENSIONS (mm)				
	Min.	Max.		
Α	15.20	1600		
В	1.90	2.10		
С	4.60	5.00		
B C D E	3.10	3.30		
Е		9.60		
F		2.00		
G H	0.35	0.55		
Н		1.40		
J	5.35	5.55		
K	20.00			
L M	19.60	20.20		
	0.95	1.25		
N		2.00		
0		3.00		
Р		4.00		
R		4.00		
S		1.80		
Т	4.80	5.20		

Pin 1 :	Base
Pin 2 :	Collector
Pin 3 :	Emitter
Package	Collector

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www.comsetsemi.com

info@comsetsemi.com